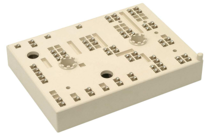
MiniSKiiP®3 PACK 1200V/150A

Features

- Solderless interconnection
- Trench Fieldstop IGBT4 technology

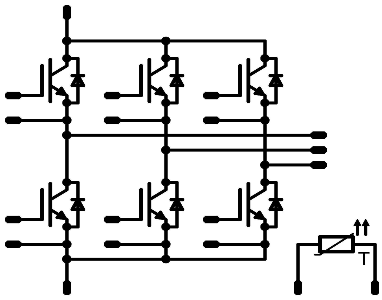
MiniSKiiP®3 housing



Target Applications

- Servo Drives
- Industrial Motor Drives
- UPS

Schematic



Types

- V23990-K430-F40-PM

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
T1,T2,T3,T4,T5,T6					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	$T_j=T_jmax$	T_h=80℃	123	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by T_jmax		450	A
Turn off safe operating area		V_{CE}≤1200V, $T_j≤T_{op\ max}$		300	A
Power dissipation per IGBT	P_{tot}	$T_j=T_jmax$	T_h=80℃	282	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150℃ V_{GE}=15V		10 600	µs V
Maximum Junction Temperature	T_jmax			175	℃
D1,D2,D3,D4,D5,D6					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_jmax$	T_h=80℃	87	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_jmax		300	A
Power dissipation per Diode	P_{tot}	$T_j=T_jmax$	T_h=80℃	175	W
Maximum Junction Temperature	T_jmax			175	℃

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	℃
Operation temperature under switching condition	T_{op}		-40…+(Tjmax - 25)	℃
Insulation Properties				
Insulation voltage	V_{is}	t=2s DC voltage	4000	V
Creepage distance			min 12.7	mm
Clearance			min 12.7	mm

Characteristic Values

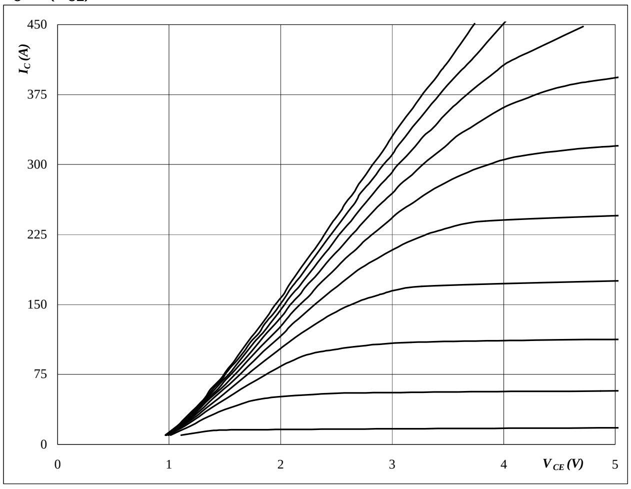
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
T1,T2,T3,T4,T5,T6										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,006	Tj=25℃ Tj=150℃	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		150	Tj=25℃ Tj=150℃	1,6	2,04 2,5	2,2	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		Tj=25℃ Tj=150℃			0,2	mA
Gate-emitter leakage current	I_{GES}		±20	0		Tj=25℃ Tj=150℃			650	nA
Integrated Gate resistor	R_{gint}							5		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=2Ω Rgon=2Ω	±15	600	150	Tj=25℃ Tj=150℃		175 193		ns
Rise time	t_r					Tj=25℃ Tj=150℃		46 53		
Turn-off delay time	$t_{d(off)}$					Tj=25℃ Tj=150℃		288 375		
Fall time	t_f					Tj=25℃ Tj=150℃		58 100		
Turn-on energy loss per pulse	E_{on}					Tj=25℃ Tj=150℃		15 23		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25℃ Tj=150℃		8,26 14,15		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25℃		8800		pF
Output capacitance	C_{oss}							580		
Reverse transfer capacitance	C_{rss}							470		
Gate charge	Q_{Gate}		±15			Tj=25℃		1250		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50µm λ=1W/mK						0,33		K/W
D1,D2,D3,D4,D5,D6										
Diode forward voltage	V_F				150	Tj=25℃ Tj=150℃	1,5	2,5 2,53	2,7	V
Peak reverse recovery current	I_{RRM}	Rgon=2Ω	±15	600	150	Tj=25℃ Tj=150℃		77 107		A
Reverse recovery time	t_{rr}					Tj=25℃ Tj=150℃		125 492		ns
Reverse recovered charge	Q_{rr}					Tj=25℃ Tj=150℃		7,99 24,3		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25℃ Tj=150℃		237 1268		A/µs
Reverse recovered energy	Erec					Tj=25℃ Tj=150℃		2,14 8,21		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50µm λ=1W/mK						0,52		K/W
Thermistor										
Rated resistance	R					T=25℃		1000		Ω
Deviation of R100	ΔR/R	R100=1670 Ω				T=100℃	-3		3	%
R100	P					T=100℃		1670,313		Ω
A-value	B(25/50)	Tol. %				T=25℃		7,635*10-3		1/K
B-value	B(25/100)	Tol. %				T=25℃		1,731*10-5		1/K²
Vincotech NTC Reference									E	

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 1 T1,T2,T3,T4,T5,T6 IGBT

Typical output characteristics

$I_C = f(V_{CE})$



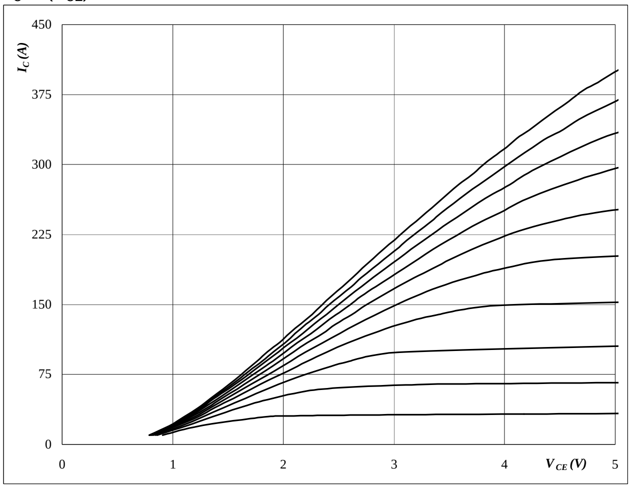
At

t_p =	350	µs
T_j =	25	℃
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 T1,T2,T3,T4,T5,T6 IGBT

Typical output characteristics

$I_C = f(V_{CE})$



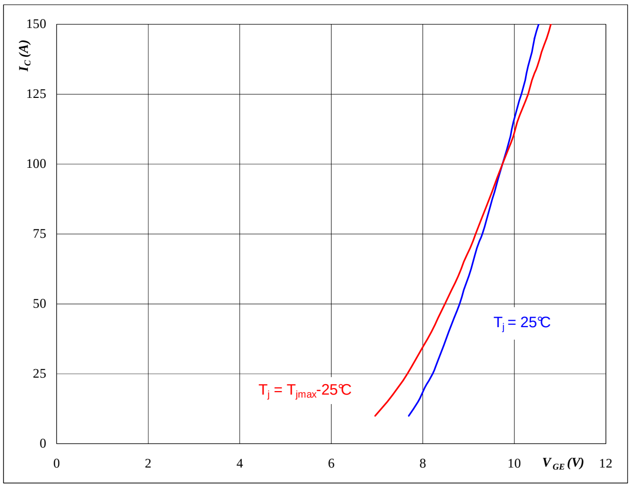
At

t_p =	350	µs
T_j =	150	℃
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 T1,T2,T3,T4,T5,T6 IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



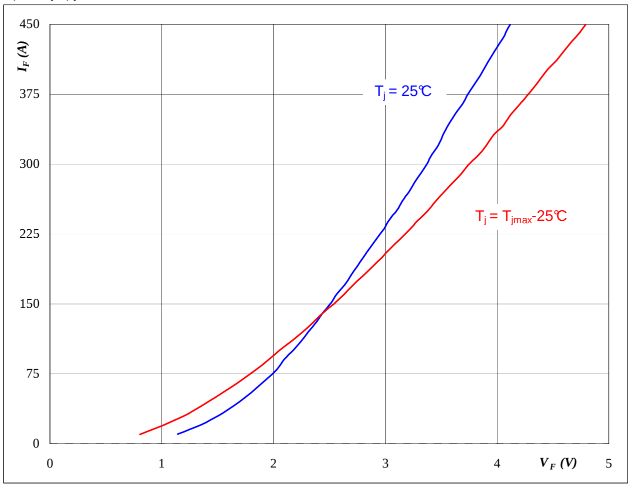
At

Tj =	25/150	℃
t_p =	350	µs
V_{CE} =	10	V

Figure 4 D1,D2,D3,D4,D5,D6 FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

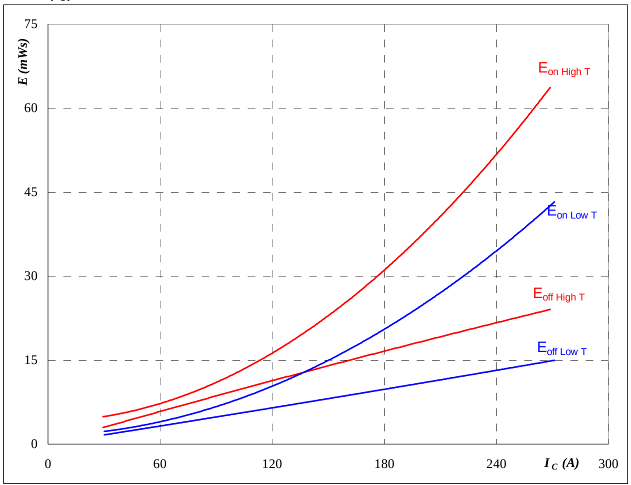
t_p =	350	µs

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 5 T1,T2,T3,T4,T5,T6 IGBT

Typical switching energy losses as a function of collector current

$E = f(I_C)$



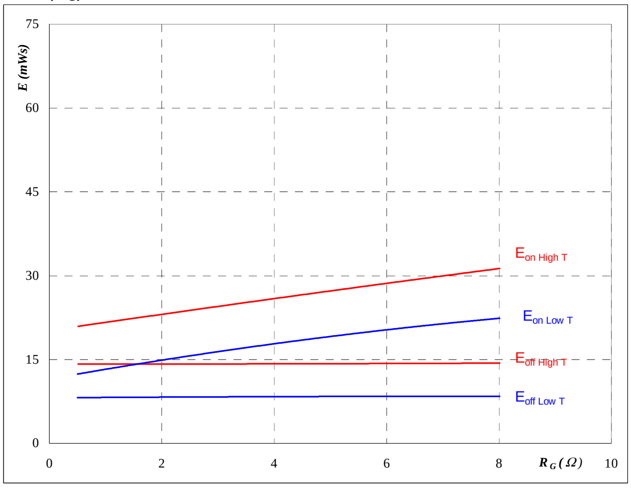
With an inductive load at

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω
R_{goff} =	2	Ω

Figure 6 T1,T2,T3,T4,T5,T6 IGBT

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$



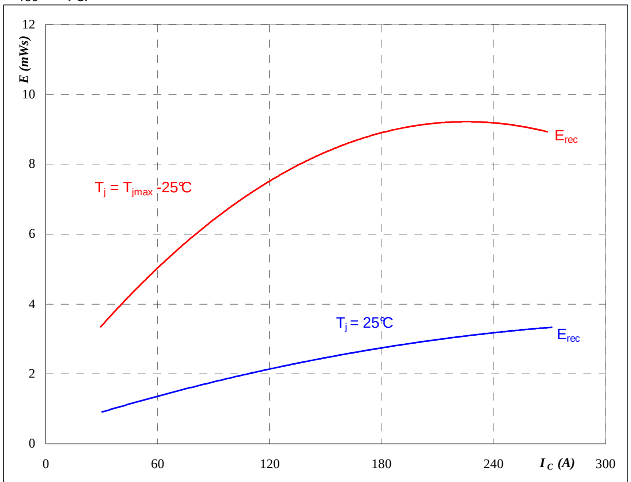
With an inductive load at

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	150	A

Figure 7 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery energy loss as a function of collector current

$E_{rec} = f(I_C)$



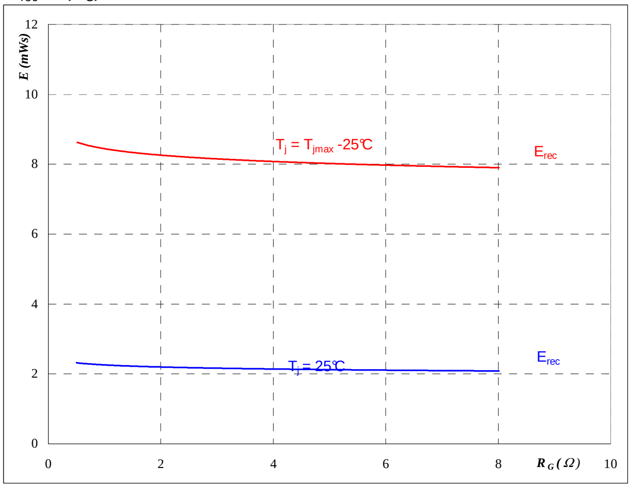
With an inductive load at

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

Figure 8 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery energy loss as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

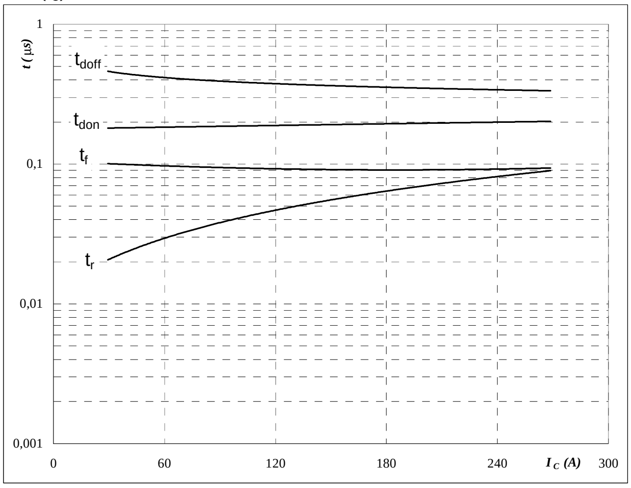
T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	150	A

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 9 T1,T2,T3,T4,T5,T6 IGBT

Typical switching times as a function of collector current

t = f(I_C)



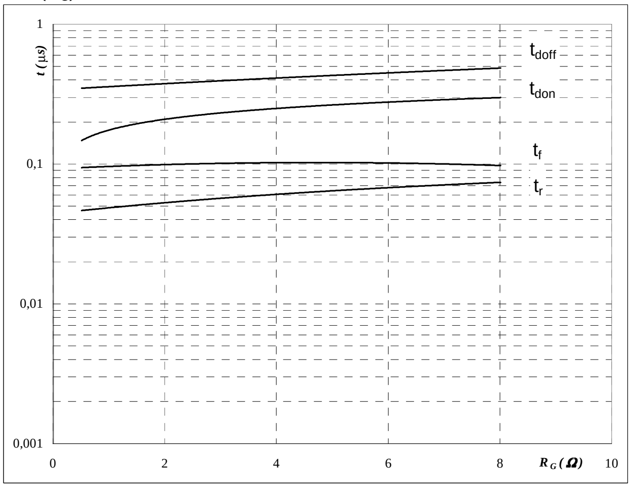
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω
R_{goff} =	2	Ω

Figure 10 T1,T2,T3,T4,T5,T6 IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



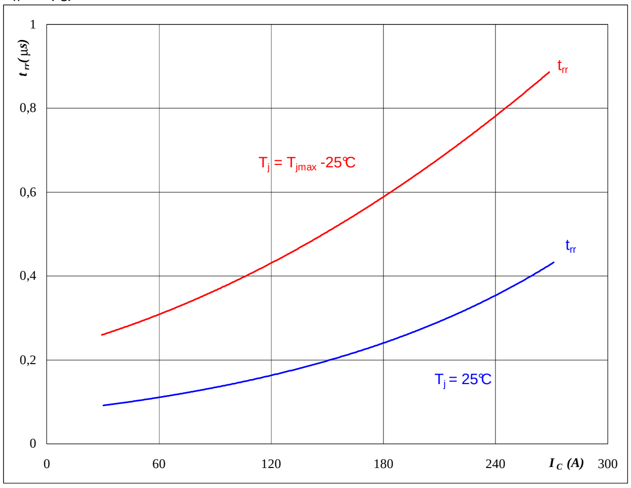
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	150	A

Figure 11 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



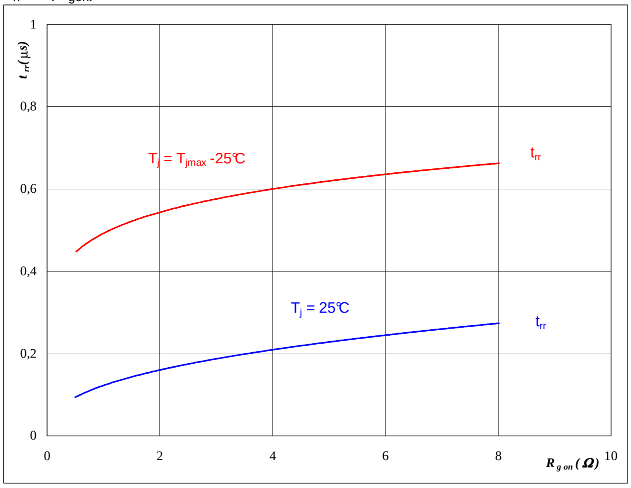
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

Figure 12 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

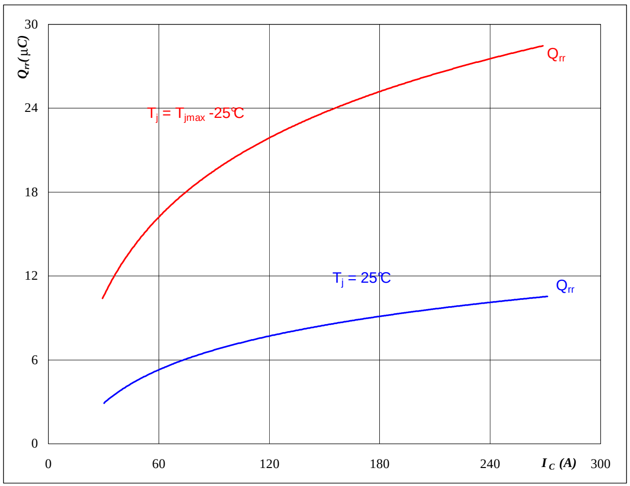
T_j =	25/150	°C
V_R =	600	V
I_F =	150	A
V_{GE} =	±15	V

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 13 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



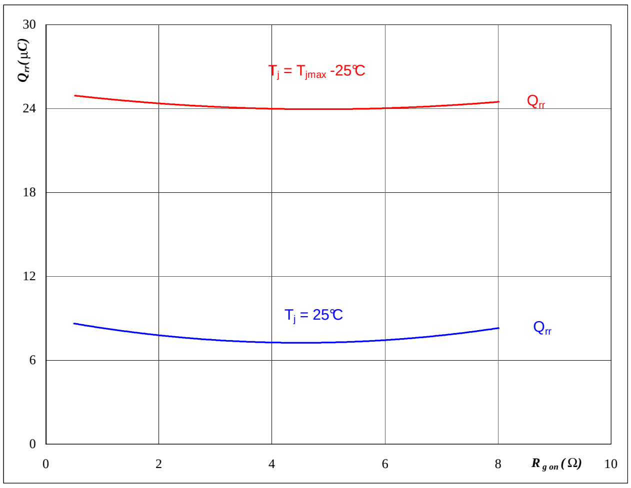
At

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

Figure 14 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



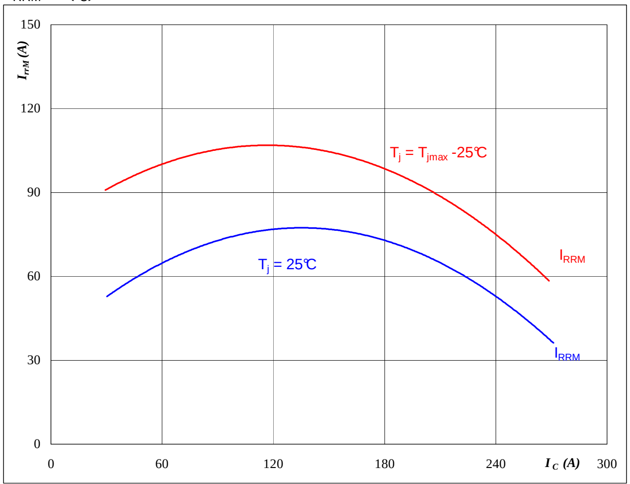
At

T_j =	25/150	℃
V_R =	600	V
I_F =	150	A
V_{GE} =	±15	V

Figure 15 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



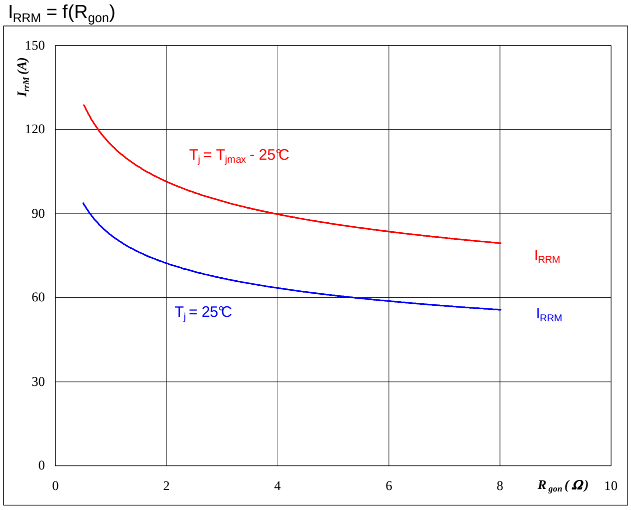
At

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

Figure 16 D1,D2,D3,D4,D5,D6 FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

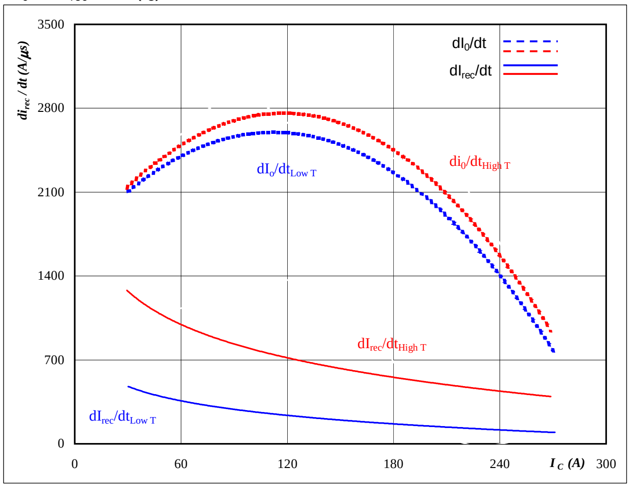
T_j =	25/150	℃
V_R =	600	V
I_F =	150	A
V_{GE} =	±15	V

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 17 D1,D2,D3,D4,D5,D6 FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



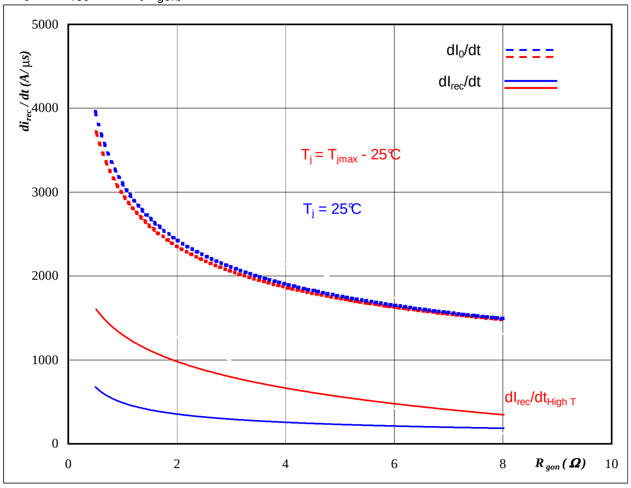
At

T_j =	25/150	℃
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

Figure 18 D1,D2,D3,D4,D5,D6 FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



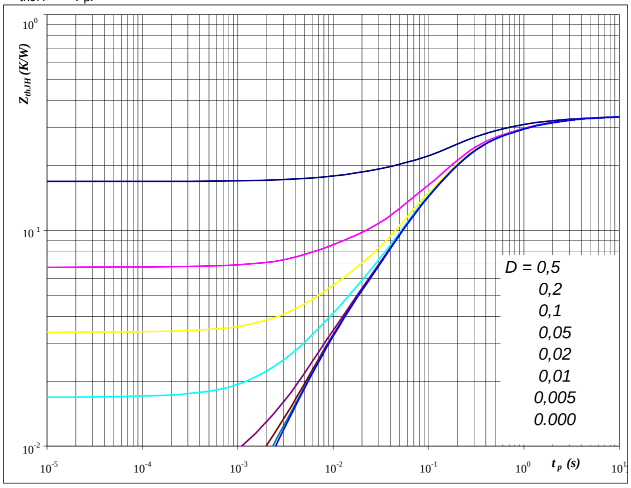
At

T_j =	25/150	℃
V_R =	600	V
I_F =	150	A
V_{GE} =	±15	V

Figure 19 T1,T2,T3,T4,T5,T6 IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T	
R_{thJH} =	0,33	K/W

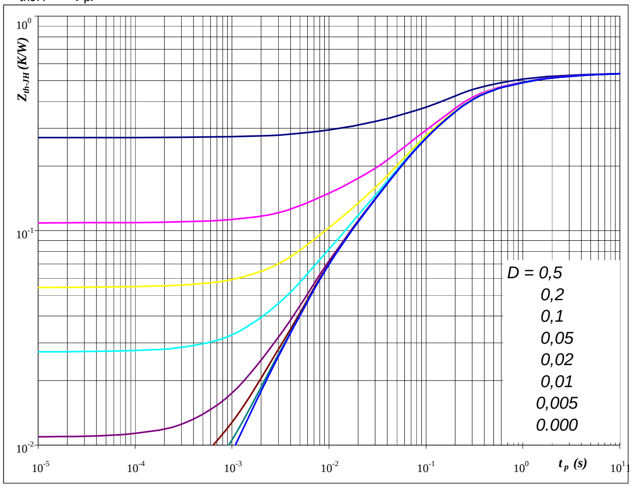
IGBT thermal model values

R (C/W)	Tau (s)
0,03	3,3E+00
0,06	9,3E-01
0,15	2,0E-01
0,08	7,9E-02
0,02	8,3E-03

Figure 20 D1,D2,D3,D4,D5,D6 FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T	
R_{thJH} =	0,52	K/W

FWD thermal model values

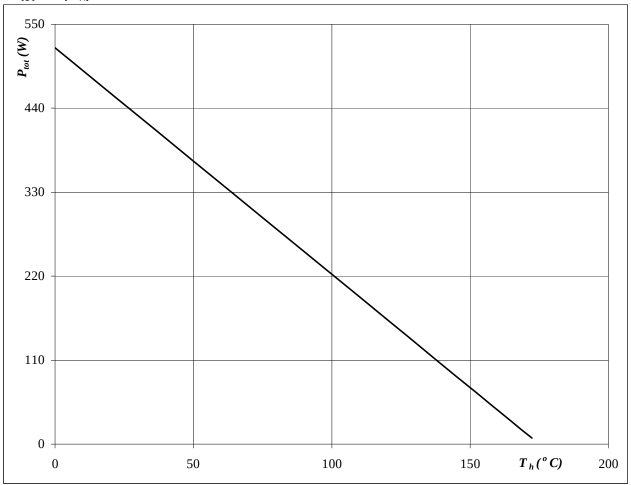
R (C/W)	Tau (s)
0,03	5,2E+00
0,07	1,1E+00
0,19	2,3E-01
0,20	8,3E-02
0,06	8,8E-03

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 21 T1,T2,T3,T4,T5,T6 IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



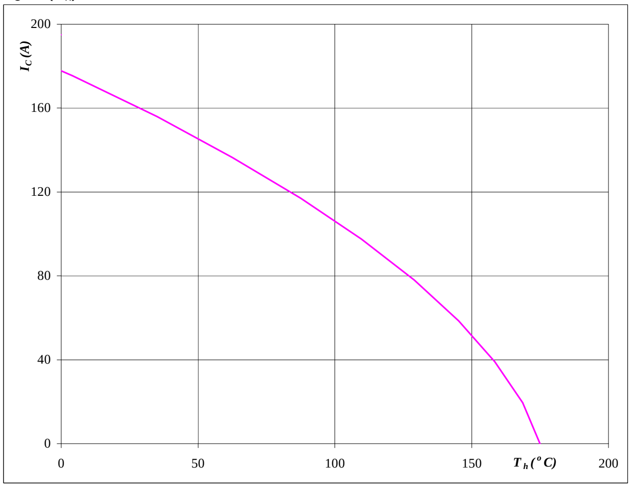
At

T_j = 175 °C

Figure 22 T1,T2,T3,T4,T5,T6 IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

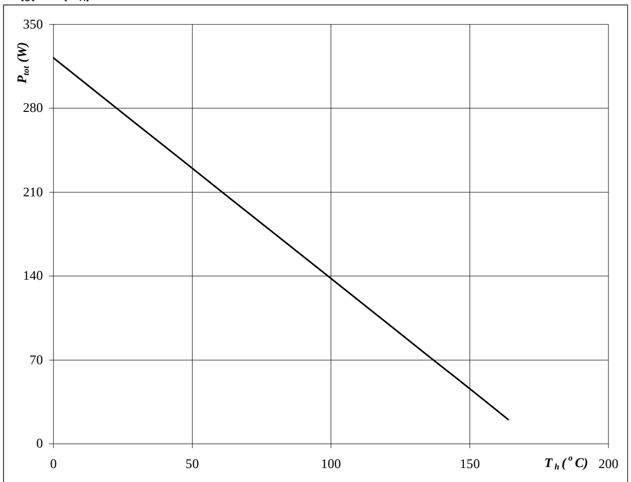
T_j = 175 °C

V_{GE} = 15 V

Figure 23 D1,D2,D3,D4,D5,D6 FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



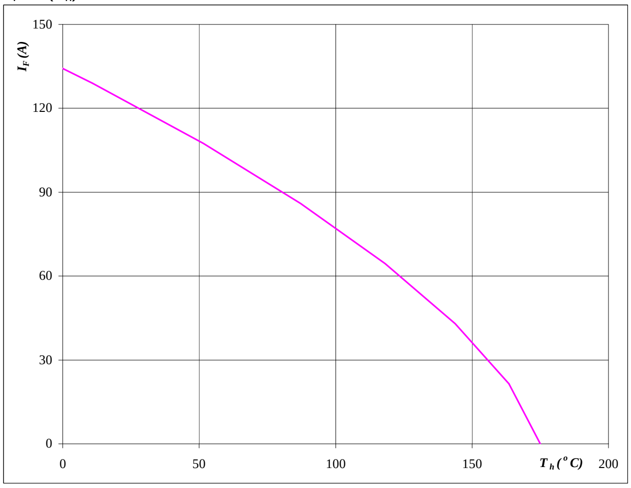
At

T_j = 175 °C

Figure 24 D1,D2,D3,D4,D5,D6 FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

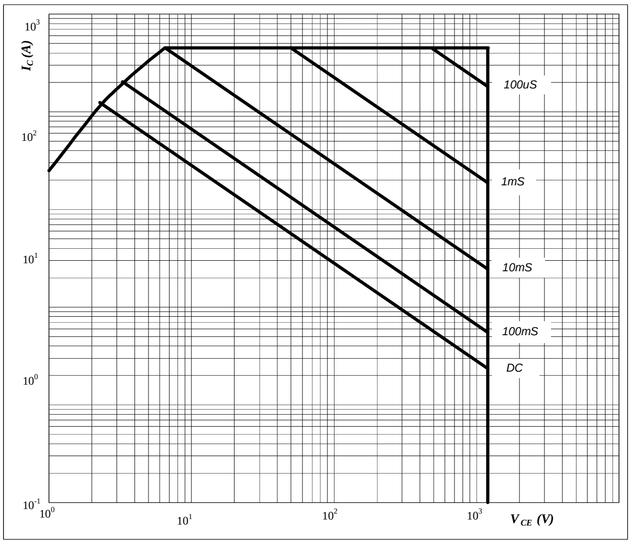
T_j = 175 °C

T1,T2,T3,T4,T5,T6/D1,D2,D3,D4,D5,D6

Figure 25 T1,T2,T3,T4,T5,T6 IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



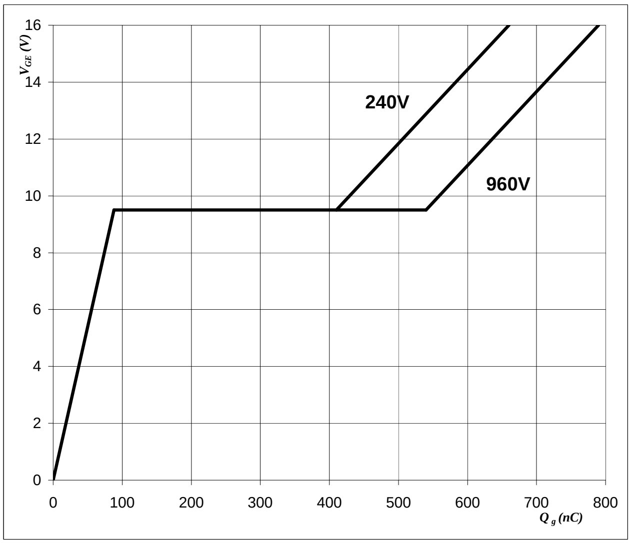
At

D =	single pulse	
T_h =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26 T1,T2,T3,T4,T5,T6 IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_{GE})$



At

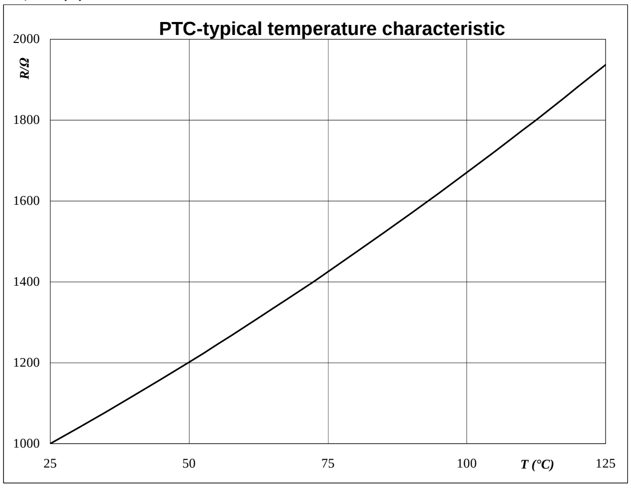
I_C =	150	A

Thermistor

Figure 1 Thermistor

Typical PTC characteristic as a function of temperature

$R_T = f(T)$



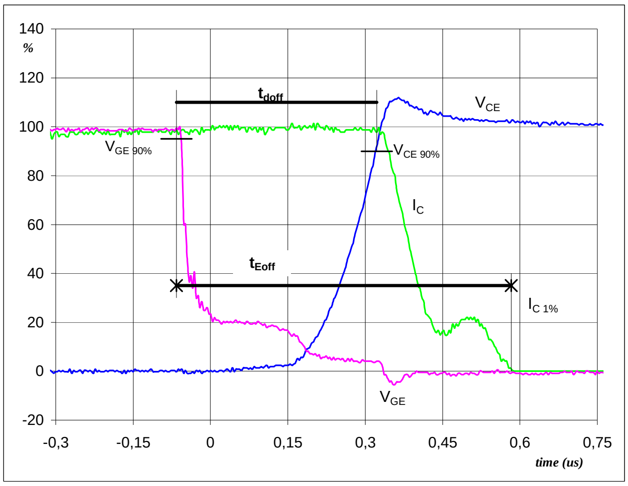
Switching Definitions Output Inverter

General conditions

T_j	=	150 °C
R_{gon}	=	2 Ω
R_{goff}	=	2 Ω

Figure 1 Output inverter IGBT

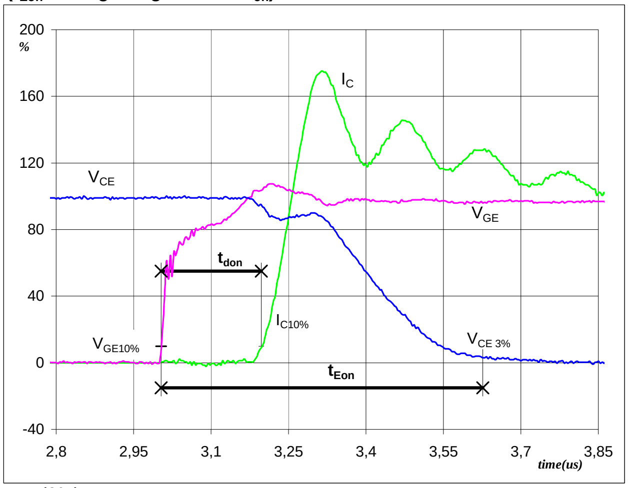
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	151	A
t_{doff} =	0,38	μs
t_{Eoff} =	0,65	μs

Figure 2 Output inverter IGBT

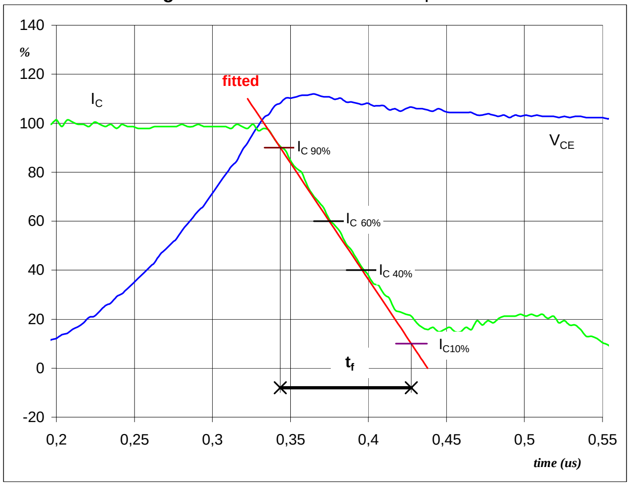
Turn-on Switching Waveforms & definition of tdon, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	151	A
t_{don} =	0,19	μs
t_{Eon} =	0,62	μs

Figure 3 Output inverter IGBT

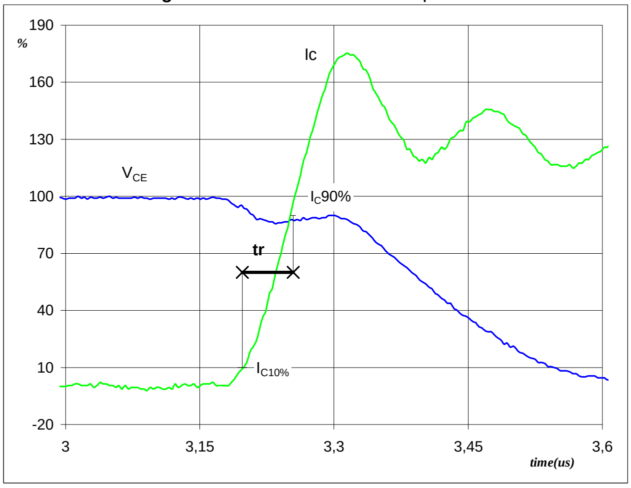
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	151	A
t_f =	0,09	μs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

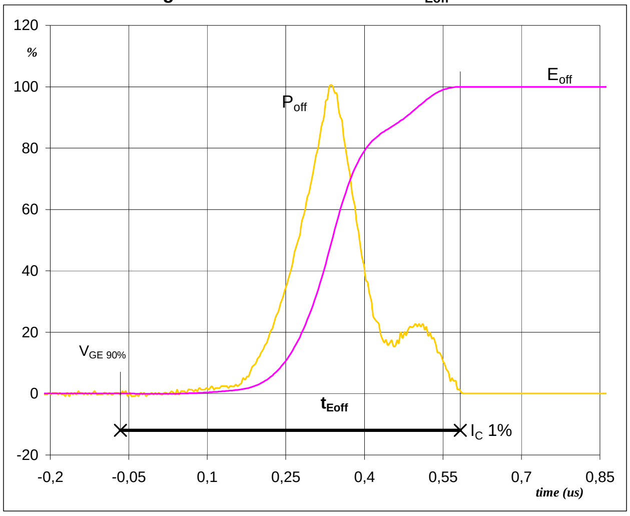


V_C (100%) =	600	V
I_C (100%) =	151	A
t_r =	0,05	μs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

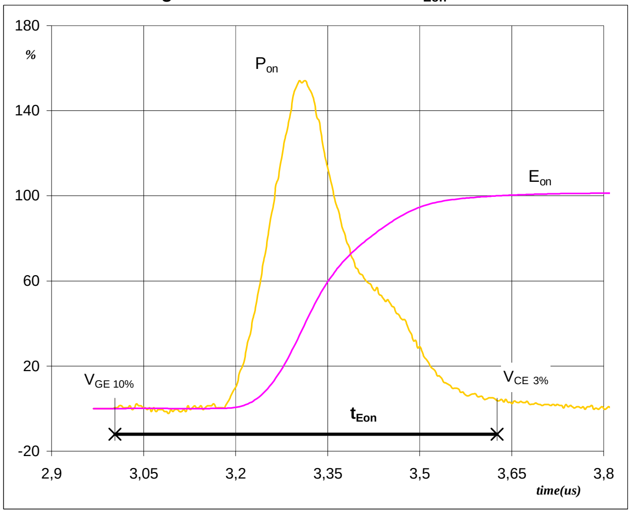
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	90,54	kW
E_{off} (100%) =	13,82	mJ
t_{Eoff} =	0,65	µs

Figure 6 Output inverter IGBT

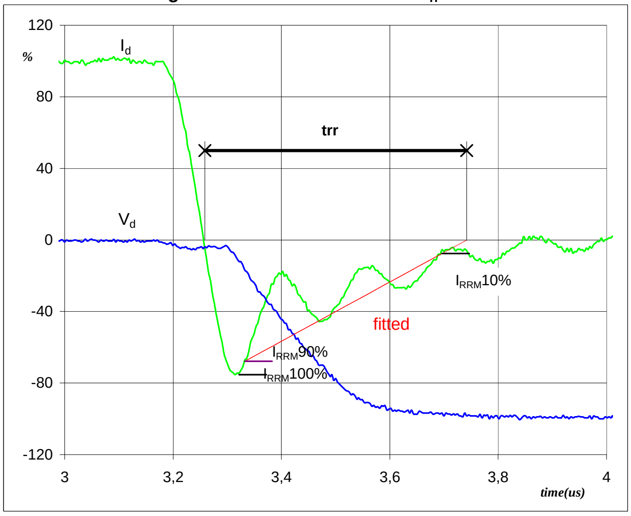
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	90,54	kW
E_{on} (100%) =	23,22	mJ
t_{Eon} =	0,62	µs

Figure 7 Output inverter IGBT

Turn-off Switching Waveforms & definition of t_{rr}

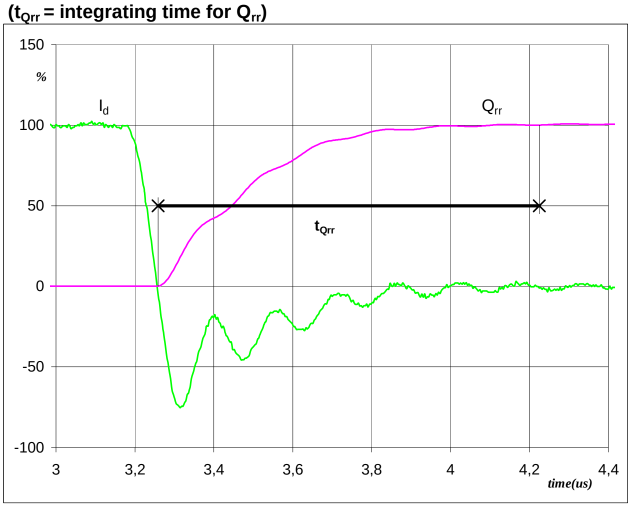


V_d (100%) =	600	V
I_d (100%) =	151	A
I_{RRM} (100%) =	-115	A
t_{rr} =	0,48	µs

Switching Definitions Output Inverter

Figure 9 Output inverter FWD

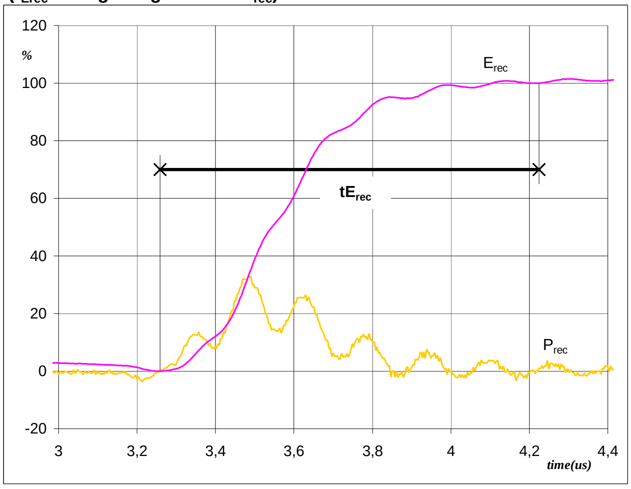
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	151	A
Q_{rr} (100%) =	24,43	μC
t_{Qrr} =	0,97	μs

Figure 10 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



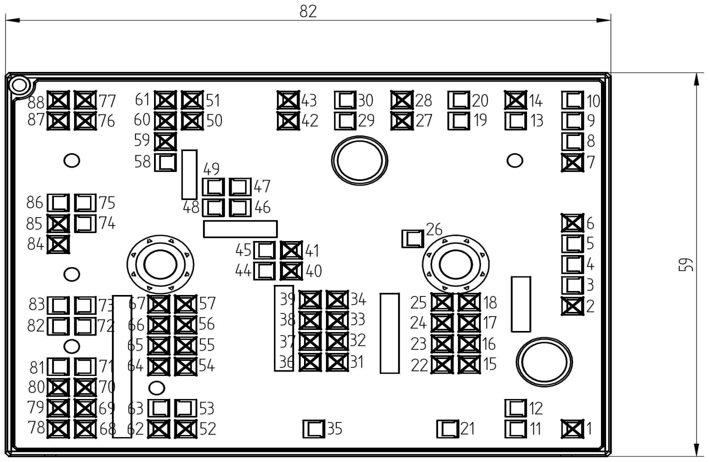
P_{rec} (100%) =	90,54	kW
E_{rec} (100%) =	8,10	mJ
t_{Erec} =	0,97	μs

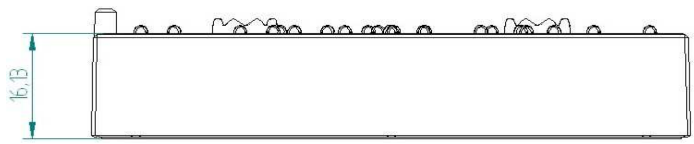
Ordering Code and Marking - Outline - Pinout

Ordering Code & Marking

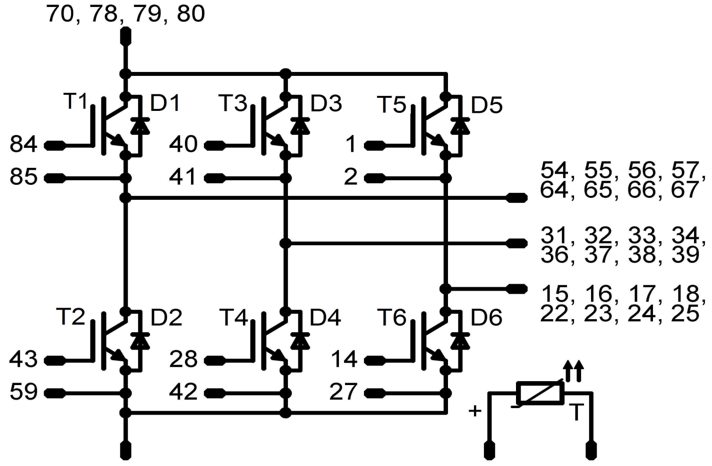
Version	Ordering Code	in DataMatrix as	in packaging barcode as
with std lid (black V23990-K32-T-PM)	V23990-K430-F40-/0A/-PM	K430F40	K430F40-/0A/
with std lid (black V23990-K32-T-PM) and P12	V23990-K430-F40-/1A/-PM	K430F40	K430F40-/1A/
with thin lid (white V23990-K33-T-PM)	V23990-K430-F40-/0B/-PM	K430F40	K430F40-/0B/
with thin lid (white V23990-K33-T-PM) and P12	V23990-K430-F40-/1B/-PM	K430F40	K430F40-/1B/

Outline





Pinout



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